

500mA 8.0kV 50nS-High Voltage Power Diodes Ultra-Fast Recovery

HVGT high voltage silicon rectifier diodes is made of high quality glass passivated chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

## SHAPE DISPLAY:

SIZE: (Unit:mm)

**DO-722 Series** 

Lead Diameter 1.2mm

22 0



HVGT NAME: DO-722

22.0

### **FEATURES:**

- 1. High reliability design.
- 2. High voltage design.
- 3. High frequency.
- 4. Conform to RoHS.
- 5. Epoxy resin molded in vacuumHave anticorrosion in the surface.
- 6. Ultra-Fast Recovery.

#### **APPLICATIONS:**

- 1. High voltage multiplier circuit
- 2. Electrostatic generator circuit .
- 3. General purpose high voltage rectifier.
- 4. Medical X-ray machine HV power supply.

#### **MECHANICAL DATA:**

- 1. Case: epoxy resin molding.
- 2. Terminal: welding axis.
- 3. Net weight: 2.3 grams (approx).

ownloaded from alldatasheet.com MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)							
Items	Symbols	Condition	Data Value	Units			
Repetitive Peak Renerse Voltage	Vrrm	Ta=25°C;	8.0	kV			
Average Output Current	IF	Ta=55°C;Resistive Load	500	mA			
Suege Current	Ifsm	Ta=25°C; 1/2 Sine(60Hz)	20	А			
Junction Temperature	TJ		-55~+150	°C			
Allowable Operation Case Temperature	Тс		125	°C			
Storage Temperature	Тѕтб		-55~+150	°C			

#### **ELECTRICAL CHARACTERISTICS:** Ta=25°C (Unless otherwise specified)

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	VF	at 25°C;I <sub>F</sub> =I <sub>F(AV)</sub>	15	V
Maximum Reverse Current	Ir1	at 25°C;Vr =Vrrm	0.5	uA
	Ir2	at 125°C;Vr =Vrrm	50	uA
Maximum Reverse Recovery Time	Trr	at 25°C; If=0.5Ir; Ir=Ifavm; Irr=0.25Ir	50	nS
Junction Capacitance	CJ	at 25°C; V <sub>R</sub> =0V; f=1MHz	7.5	pF



Unit:mm

22.0 Max



# **ESJC50-08**

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